advanced

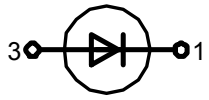
Sonic-FRD

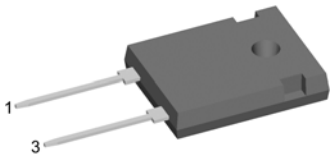
V_{RRM} = 1200 V
I_{FAV} = 20 A
t_{rr} = 75 ns

High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Single Diode

Part number

DHG 20 I 1200HA





Backside: cathode

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

TO-247AD
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

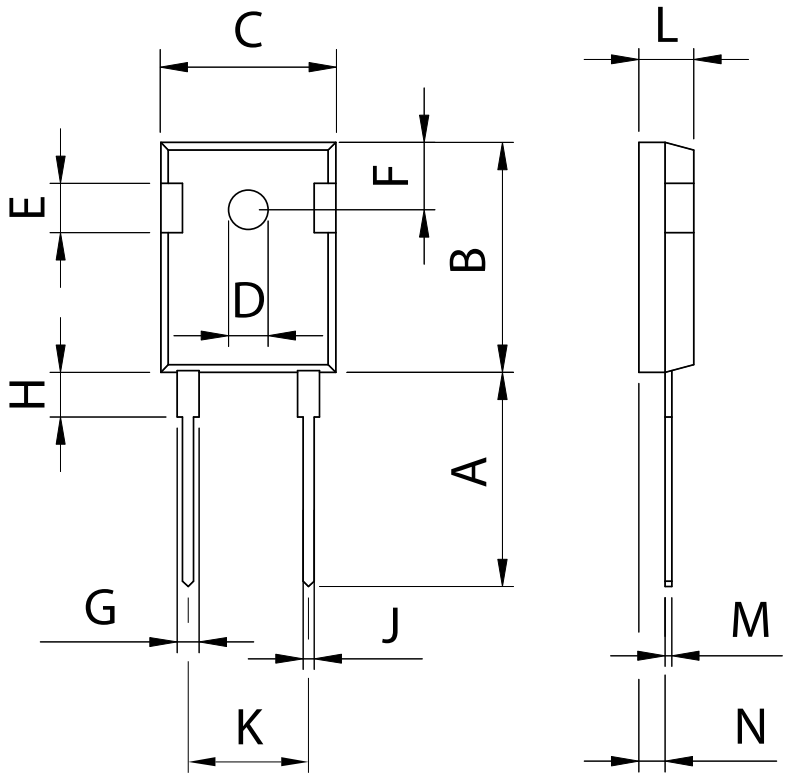
				Ratings			
Symbol	**Definition**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
V_{RRM}	*max. repetitive reverse voltage*		T_{VJ} = 25 °C			1200	V
I_R	*reverse current*	V_R = 1200 V	T_{VJ} = 25 °C			30	µA
		V_R = 1200 V	T_{VJ} = 125 °C			3	mA
V_F	*forward voltage*	I_F = 20 A	T_{VJ} = 25 °C			2.69	V
		I_F = 40 A				3.52	V
		I_F = 20 A	T_{VJ} = 125 °C			2.35	V
		I_F = 40 A				3.29	V
I_{FAV}	*average forward current*	rectangular, d = 0.5	T_C = 85 °C			20	A
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150 °C			1.60	V
r_F	*slope resistance* }					33.8	mΩ
R_{thJC}	*thermal resistance junction to case*					0.90	K/W
T_{VJ}	*virtual junction temperature*			-55		150	°C
P_{tot}	*total power dissipation*		T_C = 25 °C			140	W
I_{FSM}	*max. forward surge current*	t_p = 10 ms (50 Hz), sine	T_{VJ} = 45 °C			135	A
I_{RM}	*max. reverse recovery current*	I_F = 20 A;	T_{VJ} = 25 °C		19		A
		-di$_F$/dt = 750 A/µs	T_{VJ} = 125 °C				A
t_{rr}	*reverse recovery time*	V_R = 800 V	T_{VJ} = 25 °C		75		ns
			T_{VJ} = 125 °C				ns
C_J	*junction capacitance*	V_R = 600 V; f = 1 MHz	T_{VJ} = 25 °C		tbd		pF
E_{AS}	*non-repetitive avalanche energy*	I_{AS} = tbd A; L = 100 µH	T_{VJ} = 25 °C			tbd	mJ
I_{AR}	*repetitive avalanche current*	V_A = 1.5·V_R typ.; f = 10 kHz				tbd	A

advanced

Symbol	Definition	Conditions	Ratings min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per pin*			50	A
R_{thCH}	*thermal resistance case to heatsink*			0.25		K/W
M_D	*mounting torque*		0.8		1.2	Nm
F_C	*mounting force with clip*		20		120	N
T_{stg}	*storage temperature*		-55		150	°C
Weight				6		g

* Irms is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.
In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

Outlines TO-247AD



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

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